
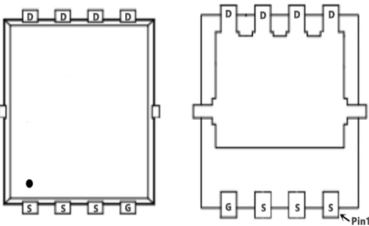




**TM60P03DF**

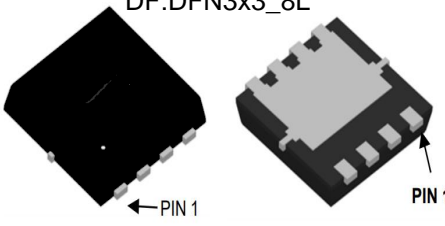
**P -Channel Enhancement Mosfet**

<p><b>General Description</b></p> <ul style="list-style-type: none"> <li>• Low <math>R_{DS(ON)}</math></li> <li>• RoHS and Halogen-Free Compliant</li> </ul> <p><b>Applications</b></p> <ul style="list-style-type: none"> <li>• Load switch</li> <li>• PWM</li> </ul>	<p><b>General Features</b></p> <p><math>V_{DS} = -30V</math> <math>I_D = -60A</math>  <math>R_{DS(ON)} = 7.5m\Omega</math> (typ.) @ <math>V_{GS} = -10V</math></p> <p>100% UIS Tested              100% <math>R_g</math> Tested</p> 
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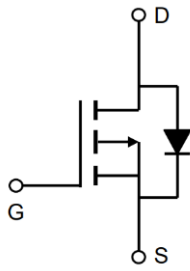


Marking:60P03D

DF:DFN3x3\_8L



PIN 1



**Absolute Maximum Ratings ( $T_A = 25^\circ C$ , unless otherwise noted)**

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D$	$T_C = 25^\circ C$	-60
		$T_C = 100^\circ C$	-30
Pulsed Drain Current <sup>1</sup>	$I_{DM}$	-168	A
Single Pulse Avalanche Energy <sup>2</sup>	<b>EAS</b>	45	mJ
Total Power Dissipation	$T_C = 25^\circ C$	$P_D$	37
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ C$

**Thermal Characteristics**

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction-to-Ambient <sup>3</sup>	$R_{\theta JA}$	75	$^\circ C/W$
Thermal Resistance from Junction-to-Case	$R_{\theta JC}$	3.36	$^\circ C/W$



# TM60P03DF

## P -Channel Enhancement Mosfet

Electrical Characteristics (T<sub>J</sub> = 25°C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
<b>Static Characteristics</b>							
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA	-30	-	-	V	
Gate-body Leakage current	I <sub>GSS</sub>	V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±20V	-	-	±100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V	T <sub>J</sub> =25°C	-	-	-1	μA
			T <sub>J</sub> =100°C	-	-	-100	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA	-1.0	-1.5	-2.5	V	
Drain-Source On-Resistance <sup>4</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10V, I <sub>D</sub> = -30A	-	7.5	14	mΩ	
		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -15A	-	10	22		
Forward Transconductance <sup>4</sup>	g <sub>fs</sub>	V <sub>DS</sub> = -5V, I <sub>D</sub> = -30A	-	57	-	S	
<b>Dynamic Characteristics<sup>5</sup></b>							
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V, f = 1MHz	-	2396	-	pF	
Output Capacitance	C <sub>oss</sub>		-	325	-		
Reverse Transfer Capacitance	C <sub>rss</sub>		-	283	-		
Gate Resistance	R <sub>g</sub>	f = 1MHz	-	10.5	-	Ω	
<b>Switching Characteristics<sup>5</sup></b>							
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> = -10V, V <sub>DS</sub> = -15V, I <sub>D</sub> = -30A	-	30	-	nC	
Gate-Source Charge	Q <sub>gs</sub>		-	5	-		
Gate-Drain Charge	Q <sub>gd</sub>		-	7.5	-		
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>GS</sub> = -10V, V <sub>DD</sub> = -15V, R <sub>G</sub> = 3Ω, I <sub>D</sub> = -30A	-	14.1	-	ns	
Rise Time	t <sub>r</sub>		-	20	-		
Turn-Off Delay Time	t <sub>d(off)</sub>		-	94	-		
Fall Time	t <sub>f</sub>		-	65	-		
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = -30A, di/dt = 100A/μs	-	19	-	ns	
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>		-	9	-	nC	
<b>Drain-Source Body Diode Characteristics</b>							
Diode Forward Voltage <sup>4</sup>	V <sub>SD</sub>	I <sub>S</sub> = -1A, V <sub>GS</sub> = 0V	-	-	-1.2	V	
Continuous Source Current	I <sub>S</sub>	T <sub>C</sub> =25°C	-	-	-60	A	

Note :

1. Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150°C.
2. The EAS data shows Max. rating . The test condition is V<sub>DD</sub>= -25V, V<sub>GS</sub>= -10V, L= 0.1mH, I<sub>AS</sub>= -30A.
3. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
5. This value is guaranteed by design hence it is not included in the production test.



Typical Characteristics

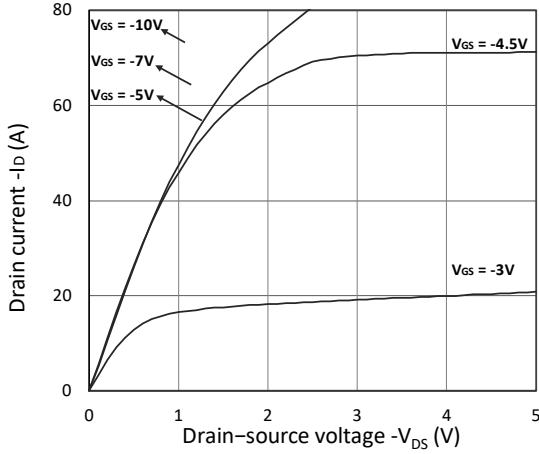


Figure 1. Output Characteristics

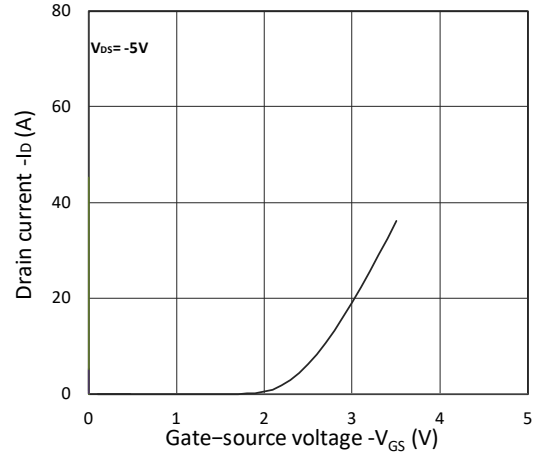


Figure 2. Transfer Characteristics

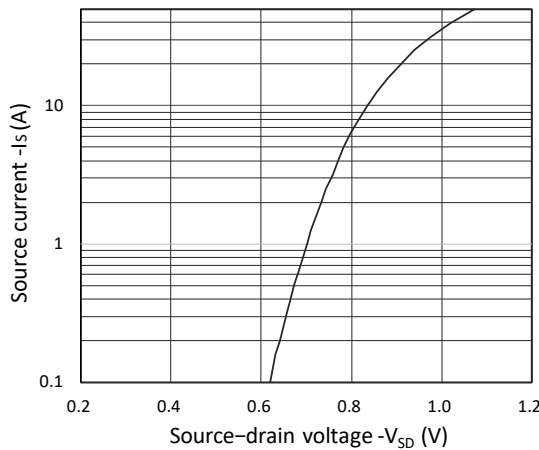


Figure 3. Forward Characteristics of Reverse

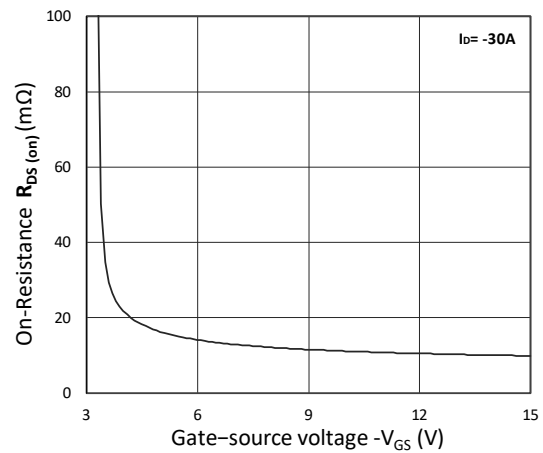


Figure 4.  $R_{DS(ON)}$  vs.  $V_{GS}$

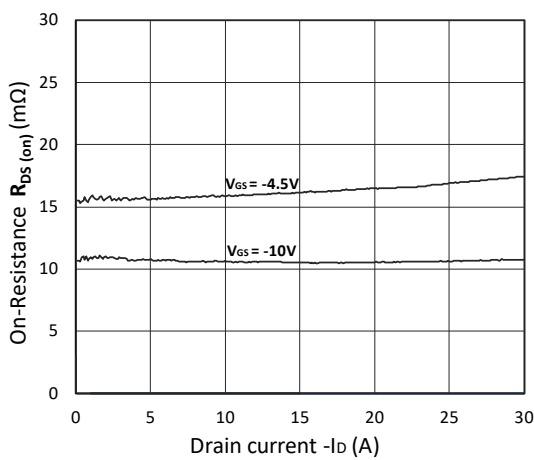


Figure 5.  $R_{DS(ON)}$  vs.  $I_D$

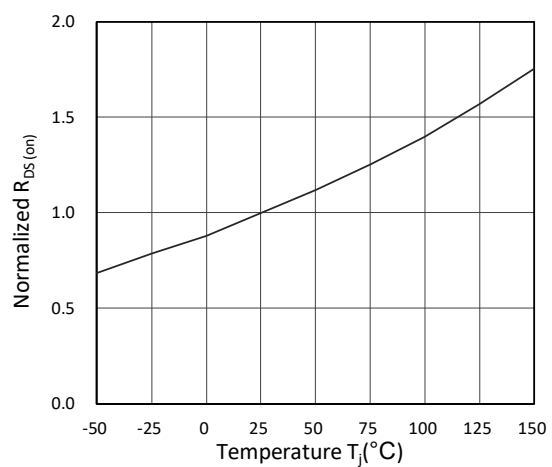


Figure 6. Normalized  $R_{DS(ON)}$  vs. Temperature



TM60P03DF

P -Channel Enhancement Mosfet

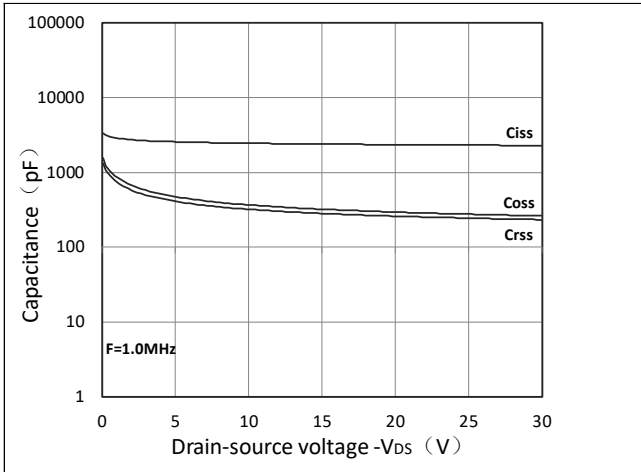


Figure 7. Capacitance Characteristics

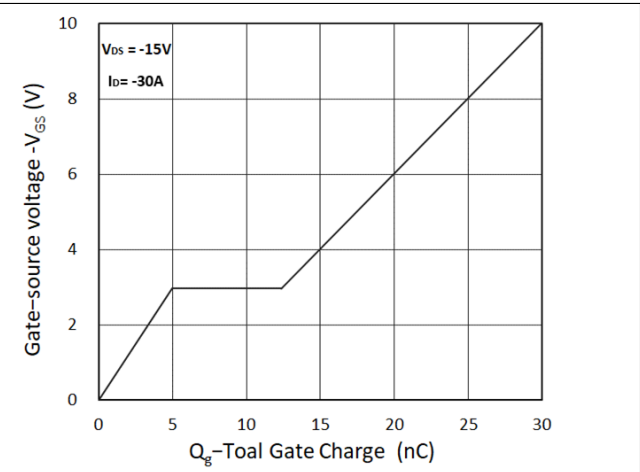


Figure 8. Gate Charge Characteristics

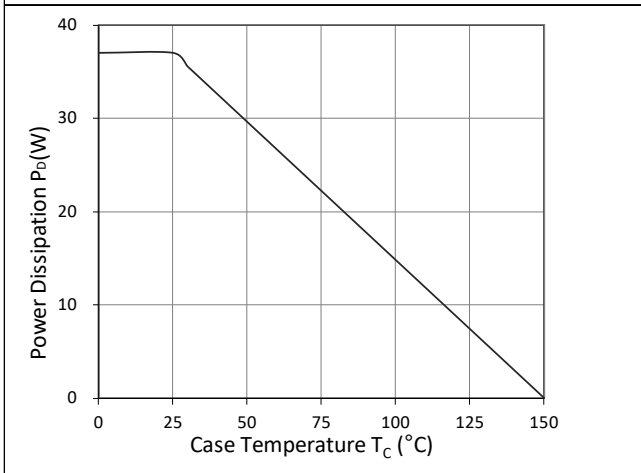


Figure 9. Power Dissipation

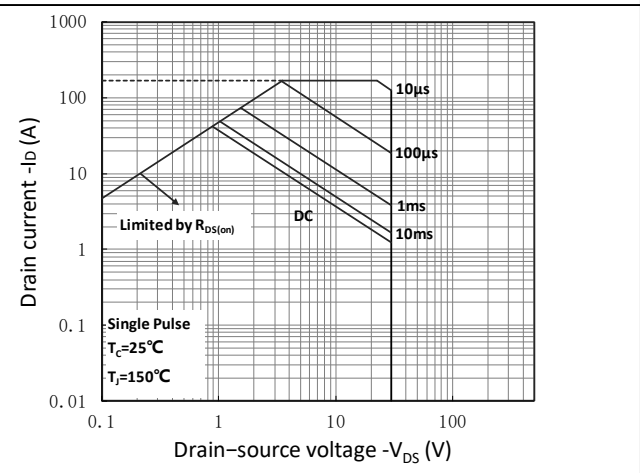


Figure 10. Safe Operating Area

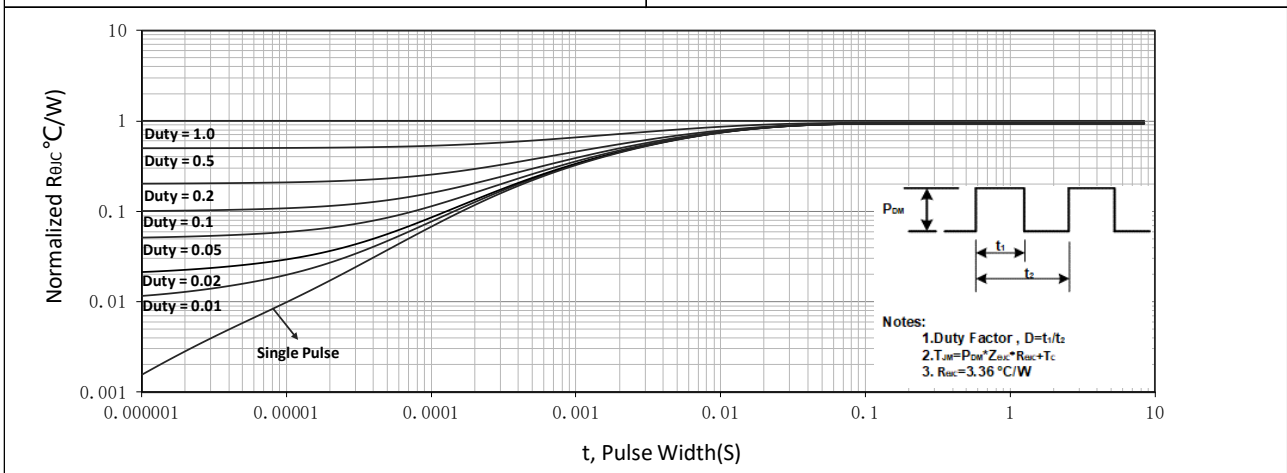


Figure 11. Normalized Maximum Transient Thermal Impedance

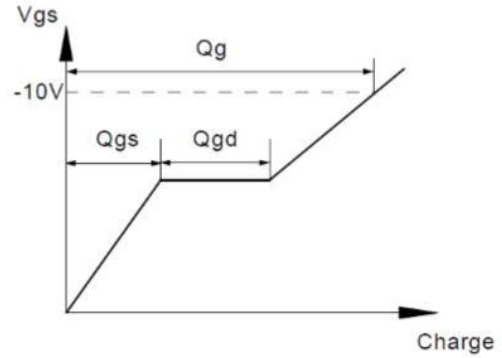
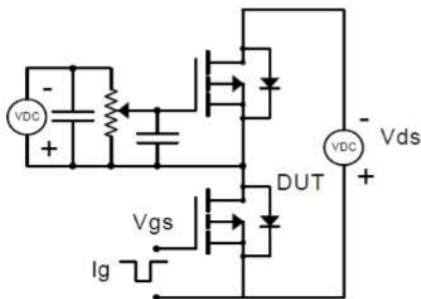


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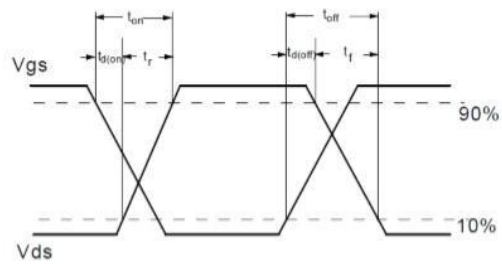
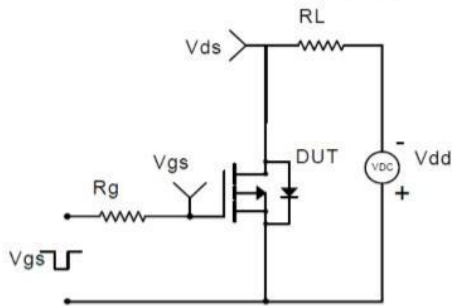
P -Channel Enhancement Mosfet

Test Circuit

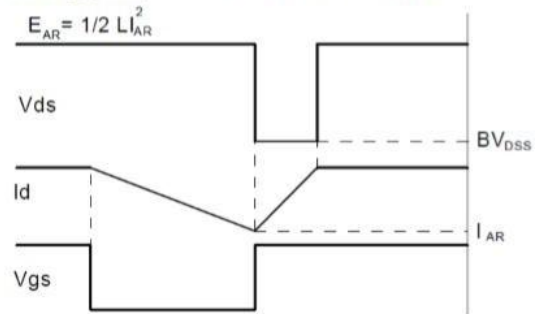
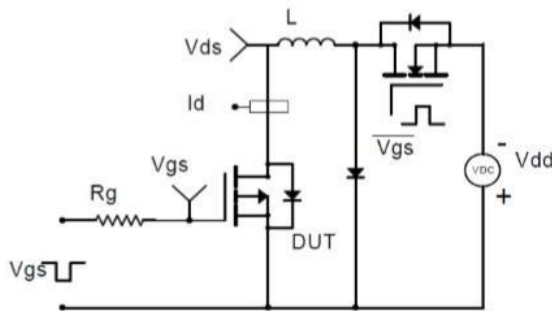
Gate Charge Test Circuit & Waveform



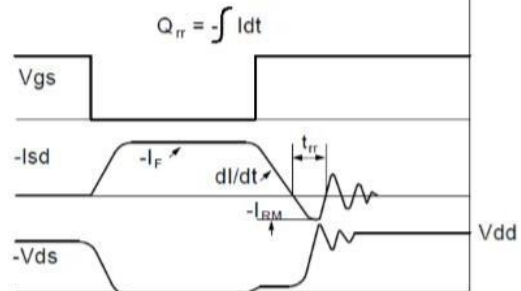
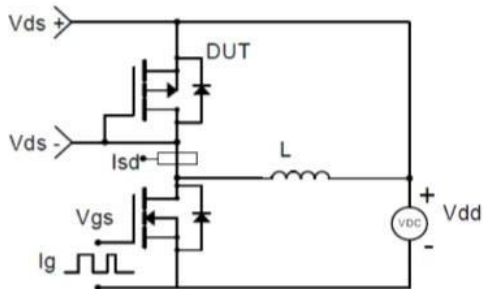
Resistive Switching Test Circuit & Waveforms



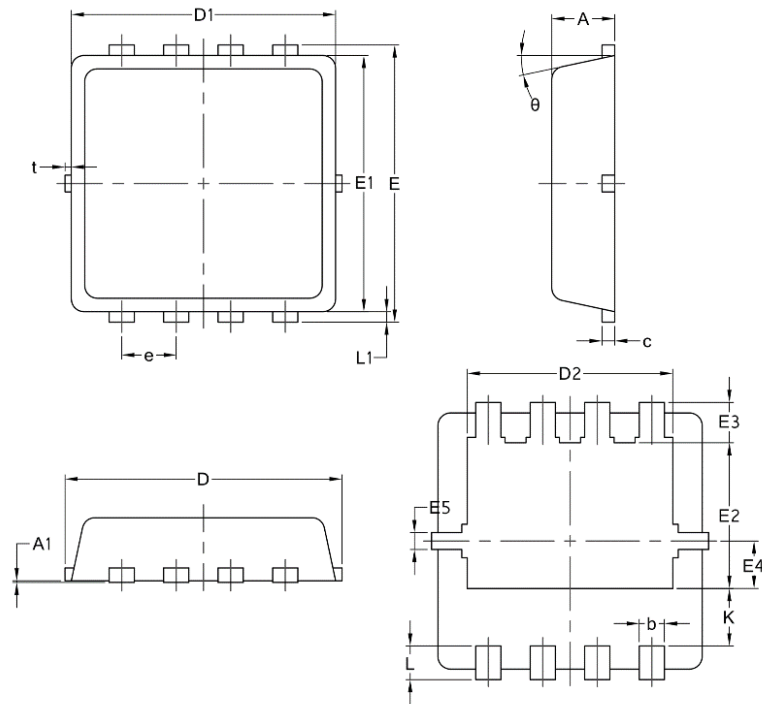
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



## Package Mechanical Data:DFN3x3-8L



Symbol	Common		
	mm		
	Mim	Nom	Max
A	0.70	0.75	0.85
A1	/	/	0.05
b	0.20	0.30	0.40
c	0.10	0.152	0.25
D	3.15	3.30	3.45
D1	3.00	3.15	3.25
D2	2.29	2.45	2.65
E	3.15	3.30	3.45
E1	2.90	3.05	3.20
E2	1.54	1.74	1.94
E3	0.28	0.48	0.65
E4	0.37	0.57	0.77
E5	0.10	0.20	0.30
e	0.60	0.65	0.70
K	0.59	0.69	0.89
L	0.30	0.40	0.50
L1	0.06	0.125	0.20
t	0	0.075	0.13
$\Phi$	10	12	14

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